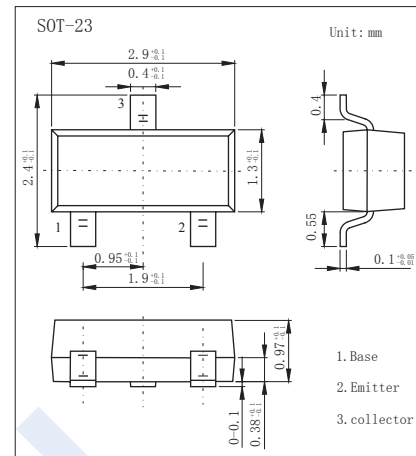


PNP Transistors

2SA1036-HF (2SA1036K-HF)

■ Features

- Large I_c . $I_{cMax.} = -500mA$
- Low $V_{CE(sat)}$. Ideal for low-voltage operation.
- Pb-Free Package May be Available. The G-Suffix Denotes a Pb-Free Lead Finish



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-40	V
Collector-emitter voltage	V_{CE0}	-32	V
Emitter-base voltage	V_{EB0}	-5	V
Collector current *	I_c	-0.5	A
Collector power dissipation	P_c	0.2	W
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

* P_c max. must not be exceeded.

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_c = -100 \mu A, I_E = 0$	-40			V
Collector- emitter breakdown voltage	V_{CE0}	$I_c = -1 mA, I_B = 0$	-32			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -100 \mu A, I_c = 0$	-5			
Collector-base cut-off current	I_{CB0}	$V_{CB} = -20 V, I_E = 0$			-100	nA
Emitter cut-off current	I_{EB0}	$V_{EB} = -4V, I_c = 0$			-100	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = -100mA, I_B = -1mA$			-0.4	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_c = -100mA, I_B = -1mA$			-1.2	
DC current gain	h_{FE}	$V_{CE} = -3V, I_c = -10mA$	82		390	
Output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		7		pF
Transition frequency	f_T	$V_{CE} = -5V, I_E = -20mA, f = 100MHz$		200		MHz

■ h_{FE} Classification

Type	2SA1036/K-P-HF	2SA1036/K-Q-HF	2SA1036/K-R-HF
Range	82-180	120-270	180-390
Marking	HP _F	HQ _F	HR _F

PNP Transistors

2SA1036-HF (2SA1036K-HF)

Typical Characteristics

